

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
20V	23mΩ @ V _{GS} = 4.5V	5.2A
	27mΩ @ V _{GS} = 2.5V	4.8A

Features and Benefits

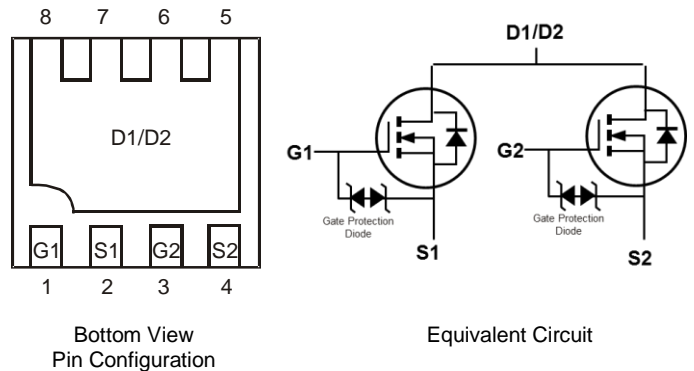
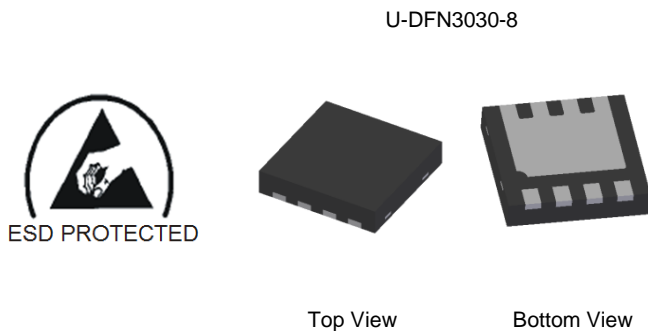
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/contact-us) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Mechanical Data

- Case: U-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Polarity: See Diagram
- Weight: 0.0172 grams (Approximate)

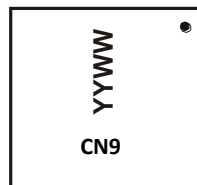


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2024UDH-7	U-DFN3030-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



CN9 = Product Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 20 for 2020)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±10	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C	I _D	5.2	A
		T _A = +70°C		4.2	
Pulsed Drain Current			I _{DM}	45	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	12	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	8	mJ

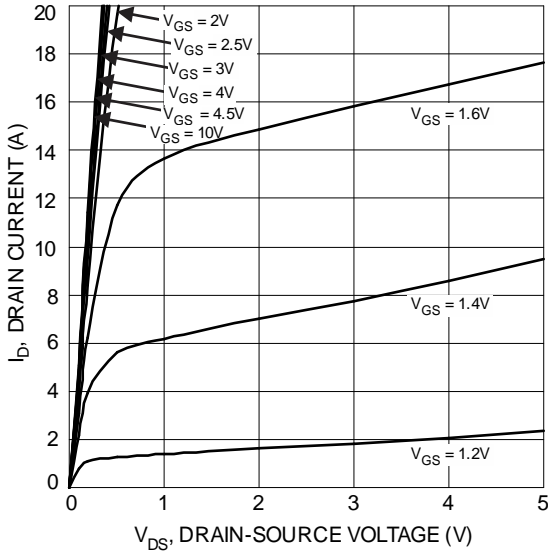
Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.95	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	132	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.76	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	71	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{θJC}	14	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

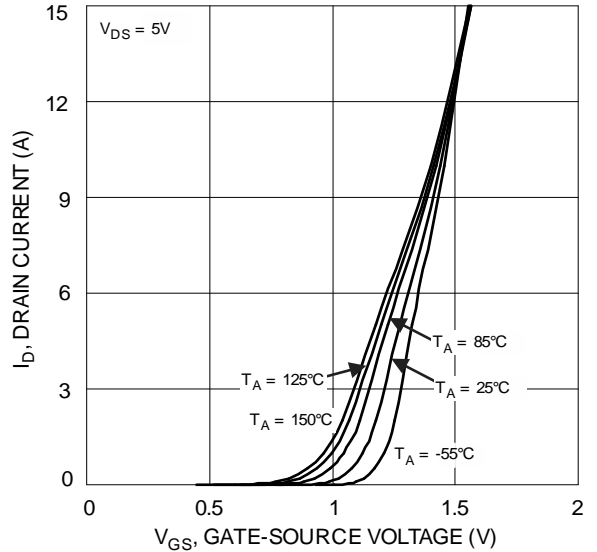
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.35	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	16	23	mΩ	V _{GS} = 4.5V, I _D = 6.5A
		—	19	27		V _{GS} = 2.5V, I _D = 5.5A
		—	24	34		V _{GS} = 1.8V, I _D = 3.5A
Diode Forward Voltage	V _{SD}	—	0.65	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	647	—	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	78	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	38	—	pF	
Gate Resistance	R _g	—	400	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	6.5	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Source Charge	Q _{gs}	—	1.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.7	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	98	—	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 10Ω, R _G = 6Ω
Turn-On Rise Time	t _r	—	140	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	1024	—	ns	
Turn-Off Fall Time	t _f	—	434	—	ns	
Reverse Recovery Time	t _{RR}	—	245	—	ns	
Reverse Recovery Charge	Q _{RR}	—	149	—	nC	I _F = 1A, di/dt = 100A/μs

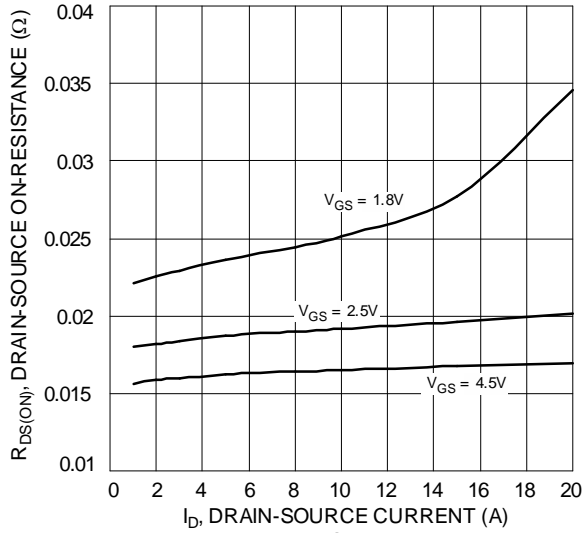
- Notes:
- Device mounted on FR-4 substrate PCB, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PCB, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.



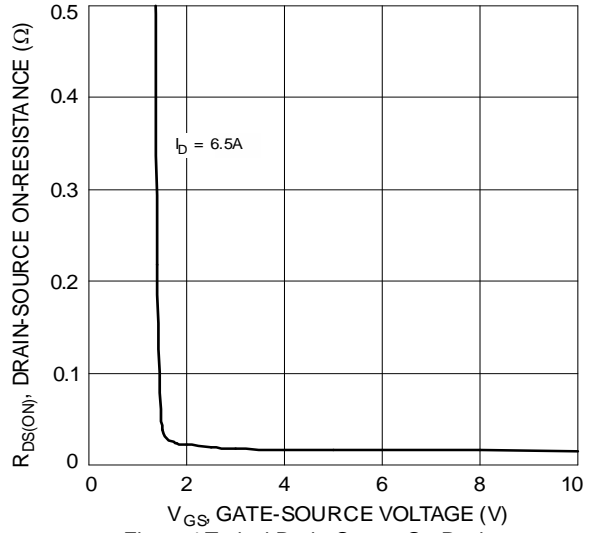
V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Figure 1 Typical Output Characteristic



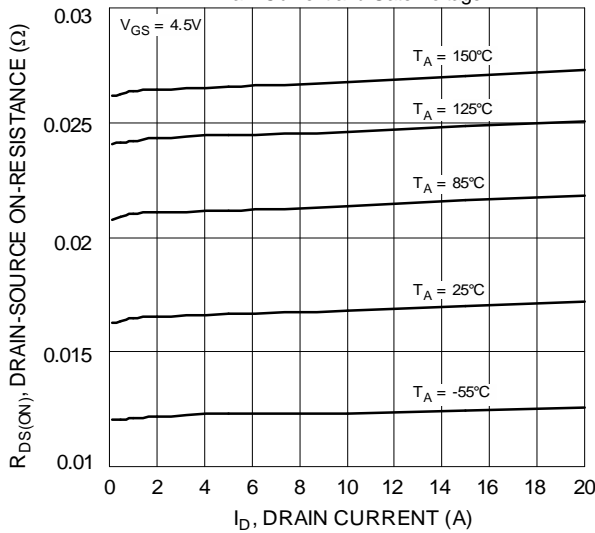
V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 2 Typical Transfer Characteristics



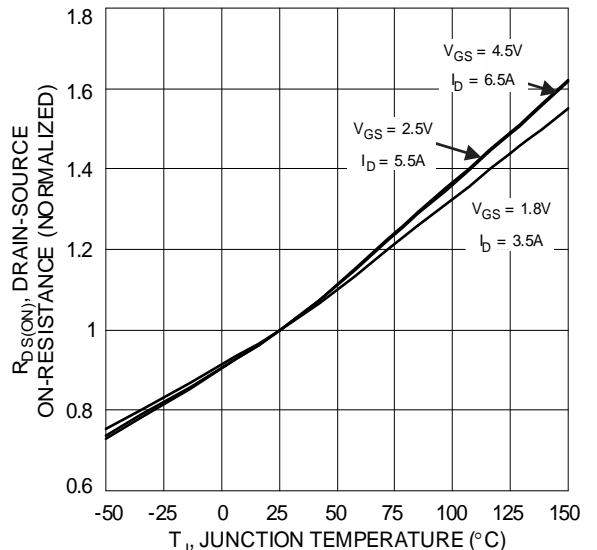
I_D , DRAIN-SOURCE CURRENT (A)
Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage



V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage



I_D , DRAIN CURRENT (A)
Figure 5 Typical On-Resistance vs. Drain Current and Temperature



T_J , JUNCTION TEMPERATURE ($^{\circ}C$)
Figure 6 On-Resistance Variation with Temperature

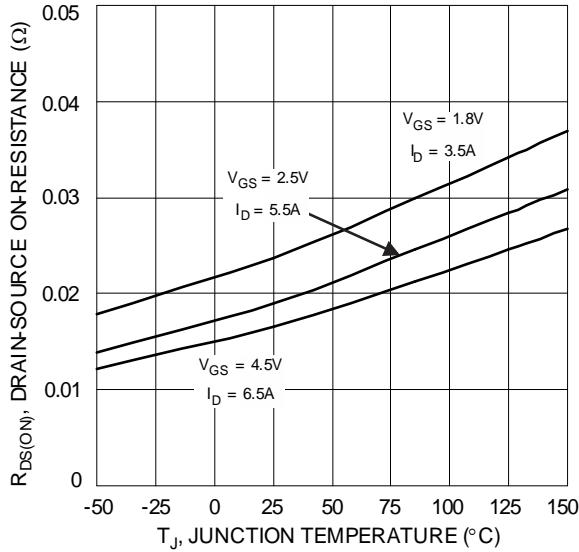


Figure 7 On-Resistance Variation with Temperature

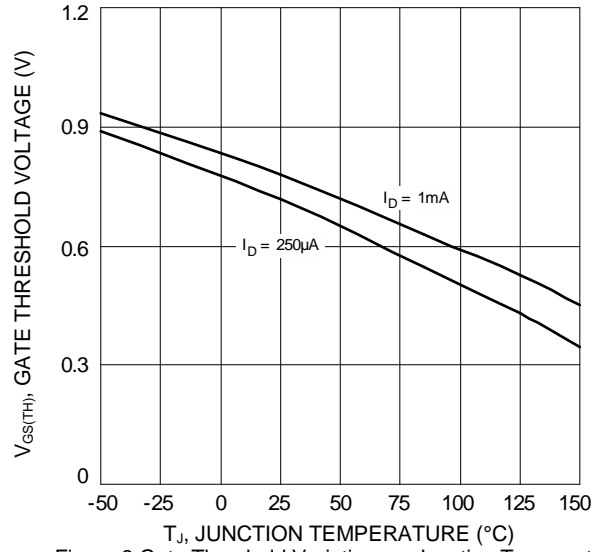


Figure 8 Gate Threshold Variation vs. Junction Temperature

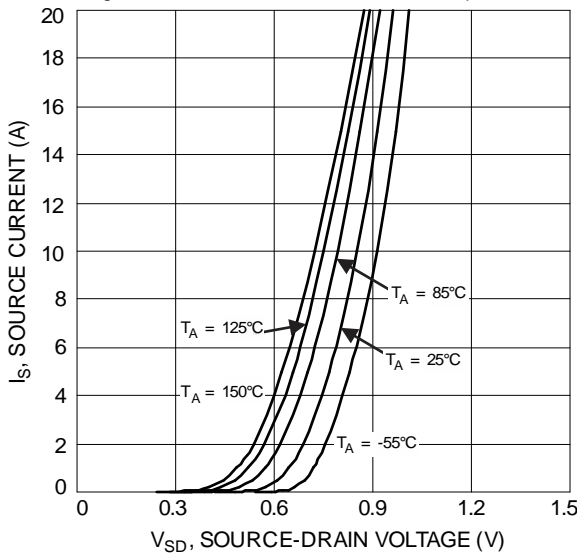


Figure 9 Diode Forward Voltage vs. Current

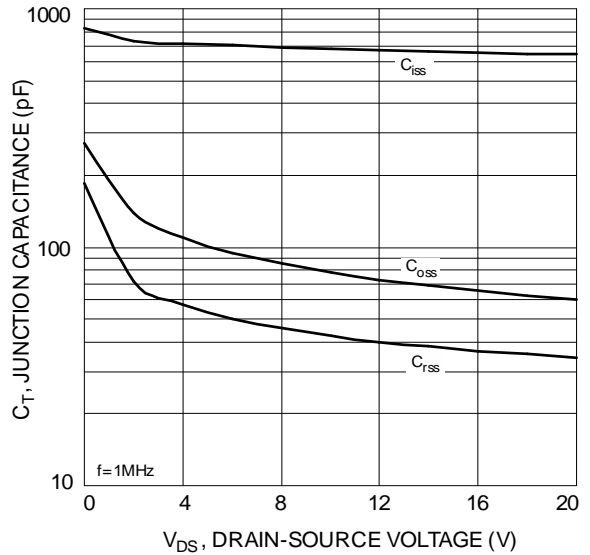


Figure 10 Typical Junction Capacitance

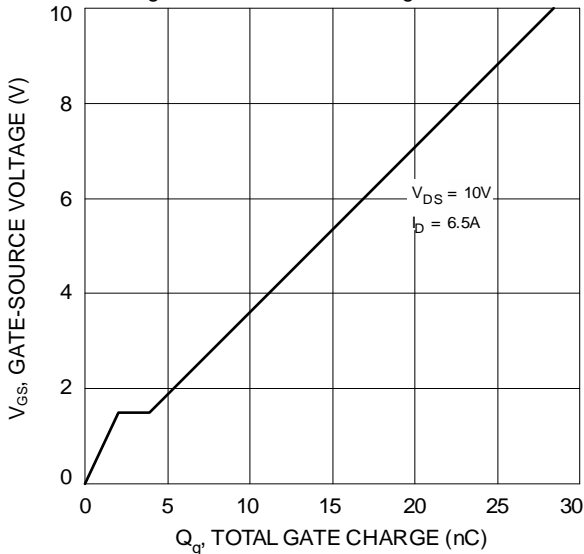


Figure 11 Gate Charge

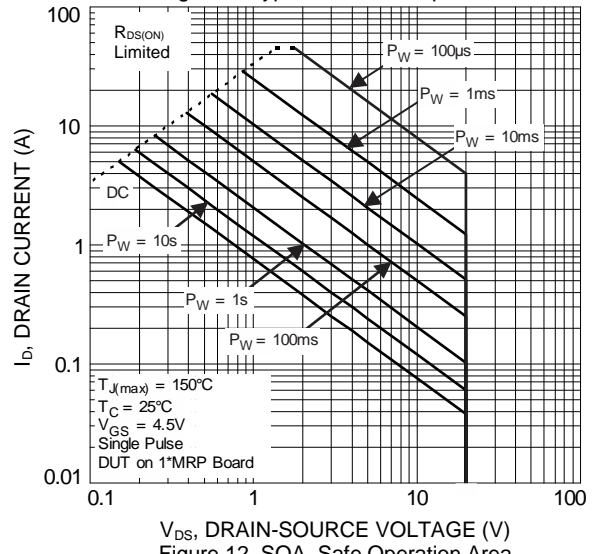
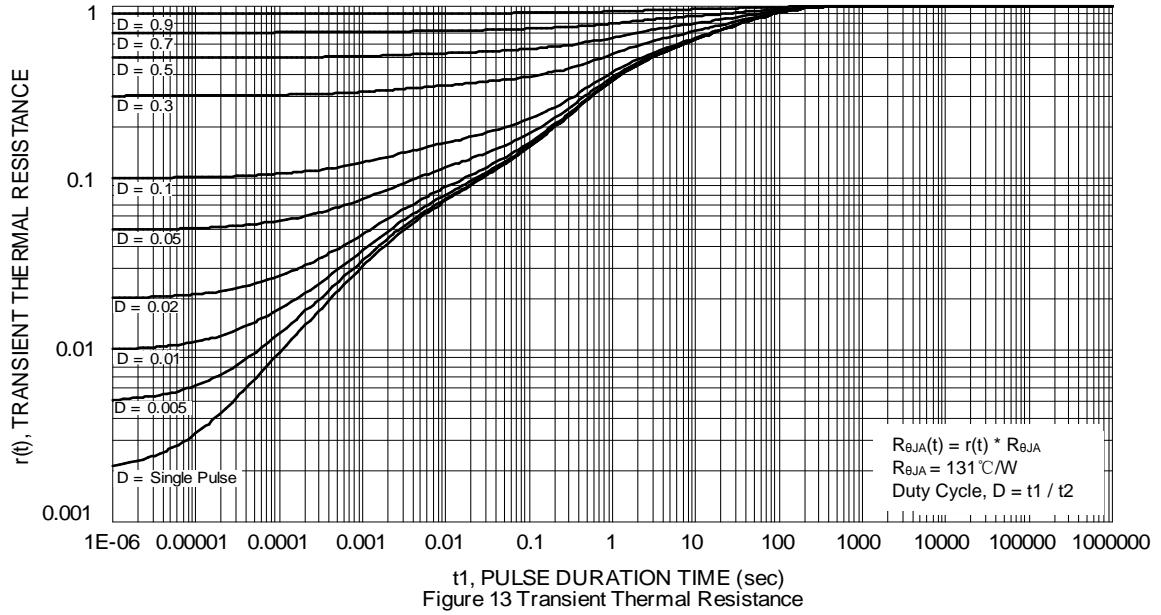


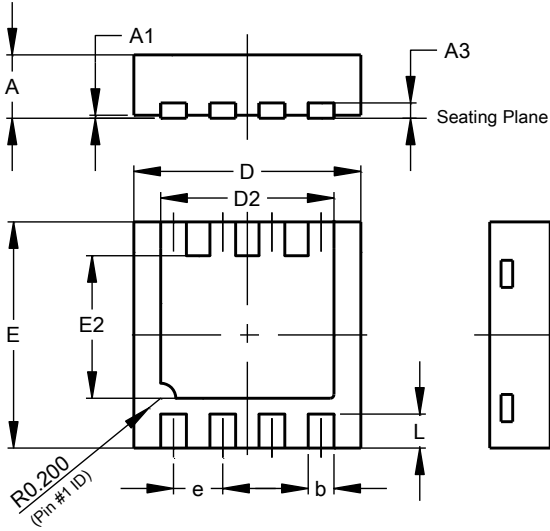
Figure 12. SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN3030-8

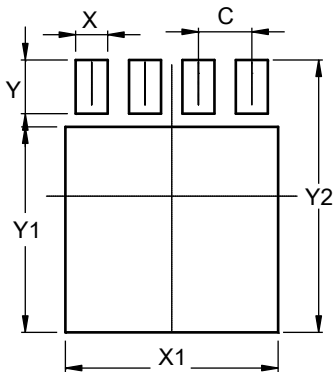


U-DFN3030-8			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.02
A3	-	-	0.15
b	0.29	0.39	0.34
D	2.90	3.10	3.00
D2	2.19	2.39	2.29
e	-	-	0.65
E	2.90	3.10	3.00
E2	1.64	1.84	1.74
L	0.30	0.60	0.45
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN3030-8



Dimensions	Value (in mm)
C	0.650
X	0.390
X1	2.590
Y	0.650
Y1	2.490
Y2	3.300

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